

BIPOLAR ANALOG INTEGRATED CIRCUITS μ PC2745T, μ PC2749T

3V-BIAS, 2.7 GHz/2.9 GHz WIDE-BAND SIMMIC AMPLIFIER FOR MOBILE COMMUNICATIONS

DESCRIPTION

 μ PC2745T and μ PC2749T are silicon monolithic integrated circuits designed as buffer amplifiers for mobile communications. These ICs feature 3V bias supply and 2.7 or 2.9 GHz wide band operation. 3 V supply operation is suitable for low voltage systems. 2.7 GHz or 2.9 GHz wide band operation is applicable for not only celular/cordless telephones but also wireless LAN and so on. Due to the 50 Ω cascadable and mini-mold package, these ICs are suitable for high-density surface mounting.

These ICs are manufactured using NEC's 20 GHz ft NESATTM III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, this series have exellent performance, uniformity and reliability.

FEATURES

• Recommended supply voltage : $Vcc = 3.0 V \pm 0.3 V$

(minimum operation voltage : μ PC2745T – Vcc = 1.8 V, μ PC2749T – Vcc = 2.7 V)

• Wide band operation : $\mu PC2745T - GP = 12 dB$, fu = 2.7 GHz

 μ PC2749T - G_P = 16 dB, fu = 2.9 GHz

• Noise Figure : μ PC2745T – NF = 6.0 dB @ 0.5 GHz, NF = 5.5 dB @ 1.0 GHz

 μ PC2749T – NF = 3.2 dB @ 0.9 GHz, NF = 4.0 dB @ 1.9 GHz

• Isolation : μ PC2745T – ISL = 38 dB @ 0.5 GHz

 μ PC2749T – ISL = 30 dB @ 1.9 GHz

• 50 Ω cascadable : 50 Ω input/output impedance

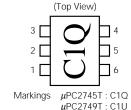
· High-density surface mounting: 6 pin mini mold package

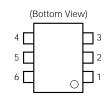
OPDERING INFORMATION

PART NUMBER	PACKAGE	SUPPLYING FORM
μPC2745T-E3 μPC2749T-E3	6 pin mini mold	Embossed tape 8 mm wide. Pin 1, 2, 3 face to perforation side of the tape. QTY 3 kp/reel.

Caution To order evaluation samples, please contact your local NEC sales office. (Part number: μ PC2745T, μ PC2749T)

PIN CONNECTION





Pin No Pin name

1 Input
2 GND
3 GND
4 Output
5 GND
6 Vcc

Caution Electro-static sensitive devices

The information in this document is subject to change without notice.

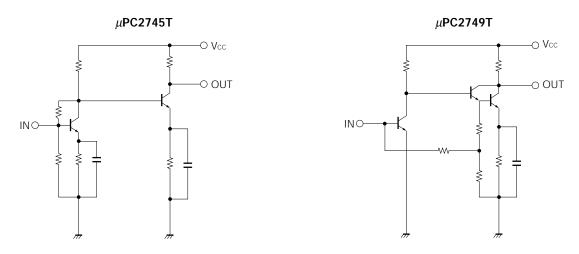


Selector Guide (T_A = +25 °C, Z_L = Z_S = 50 Ω)

TYPE	PART NUMBER	Vcc (V)	Icc (mA)	G ^p (dB)	fu (GHz)	NF (dB)	ISL (dB)	P _{O(sat)} (dBm)
5 V, 13 dB gain	μPC2711T	4.5 - 5.5	12	13	2.9	5.0	30	+1
5 V, 20 dB gain	μPC2712T	4.5 - 5.5	12	20	2.6	4.5	33	+3
3 V, 13 dB gain	μPC2745T	(1.8 -) 2.7 - 3.3	7.5	12	2.7	6.0	38	-1
3 V, 16 dB gain	μPC2749T	2.7 - 3.3	6	16	2.9	4.0	30	-6

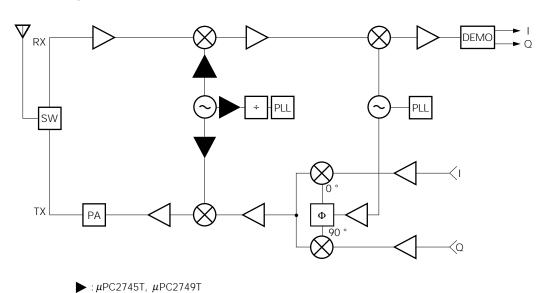
Note 1 Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

EQUIVALENT CIRCUITS



SYSTEM APPLICATION EXAMPLE

Digital cellular telephone



This system diagram presents schematic application only of these ICs. Suitable IC and block can be chosen in accordance with required RF performance on customer's systems.



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT	CONDITIONS
Supply Voltage	Vcc	4.0	V	T _A = +25 °C
Circuit Current	Icc	15 Note 2	mA	T _A = +25 °C
Power Dissipation	P _D	280	mW	Mounted on $50 \times 50 \times 1.6$ mm double side copper clad epoxy glass PWD T _A = $+85$ °C
Operating Temperature	Та	-40 to +85	°C	
Storage Temperature	T _{stg}	-55 to +150	°C	
Input Power	Pin	0	dBm	T _A = +25 °C

Note 2 μ PC2745T: 16 mA

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	MN.	TYP.	MAX.	UNIT
Supply Voltage	Vcc	2.7	3.0	3.3	٧
Operating Temperature	Та	-40	+25	+85	°C

ELECTRICAL CHARACTERISTICS (T_A = +25 $^{\circ}$ C, Vcc = 3.0 V, Z_L = Zs = 50 Ω)

DADAMETED	CVAADOL	μPC2745T		μPC2749T				CONDITION		
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNIT	CONDITION	
Circuit Current	Icc	5.0	7.5	10.0	4	6	8	mA	No input signals	
Power Gain	G₽	9.0	12	14	13	16	18.5	dB	Note 3	
Noise Figure	NF		6	7.5		4.0	5.5	dB	Note 3	
Upper Limit Operating Frequency	fu	2.3	2.7		2.5	2.9		GHz	3 dB less than the gain at 0.1 GHz	
Isolation	ISL	33	38		25	30		dB	Note 3	
Input Return Loss	RLin	8	11		7	10		dB	Note 3	
Output Return Loss	RLout	2.5	5.5		9.5	12.5		dB	Note 3	
Saturated output power	Po(sat)	-4	-1		-9	-6		dBm	Note 3 Pin = -6 dBm	

Note 3 Specified frequency condition: μ PC2745T – f = 500 MHz, μ PC2749T – f = 1.9 GHz

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STANDARD CHARACTERISTICS FOR REFERENCE (TA = +25 °C, ZL = ZS = 50 Ω)

			μPC2745T		
PARAMETER	SYMBOL	CONDITION	REFERENCE VALUE	UNIT	
Circuit Current	Icc	Vcc = 1.8 V, No input signals	4.5	mA	
Power Gain	G₽	Vcc = 3.0 V, f = 1 GHz Vcc = 3.0 V, f = 2 GHz Vcc = 1.8 V, f = 500 MHz	12 11 7	dB	
Noise Figure	NF	Vcc = 3.0 V, f = 1 GHz Vcc = 3.0 V, f = 2 GHz Vcc = 1.8 V, f = 500 MHz	5.5 5.7 8.0	dB	
Upper Limit Operating Frequency	fu	Vcc = 1.8 V, 3 dB less than the gain at 0.1 GHz	1.8	GHz	
Isolation	ISL	Vcc = 3.0 V, f = 1 GHz Vcc = 3.0 V, f = 2 GHz Vcc = 1.8 V, f = 500 MHz	33 30 35	dB	
Input Return Loss	RLin	Vcc = 3.0 V, f = 1 GHz Vcc = 3.0 V, f = 2 GHz Vcc = 1.8 V, f = 500 MHz	13 14 6.5	dB	
Output Return Loss	RLout	Vcc = 3.0 V, f = 1 GHz Vcc = 3.0 V, f = 2 GHz Vcc = 1.8 V, f = 500 MHz	6.5 8.5 6.0	dB	
Saturated Output Power	Po(sat)	Vcc = 3.0 V, f = 1 GHz, Pin = -6 dBm Vcc = 3.0 V, f = 2 GHz, Pin = -6 dBm Vcc = 1.8 V, f = 500 MHz, Pin = -10 dBm	-2.5 -3.5 -11	dBm	
3rd Order Intermodulation Distortion	IM ₃	$Vcc = 3.0 \text{ V, } P_{out} = -20 \text{ dBm, } f_1 = 500 \text{ MHz,} \\ f_2 = 502 \text{ MHz} \\ Vcc = 3.0 \text{ V, } P_{out} = -20 \text{ dBm, } f_1 = 1000 \text{ MHz,} \\ f_2 = 1002 \text{ MHz}$	-54 -50	dBc	
		$Vcc = 1.8 \text{ V}, Pout = -20 \text{ dBm}, f_1 = 500 \text{ MHz},$ $f_2 = 502 \text{ MHz}$	-31		

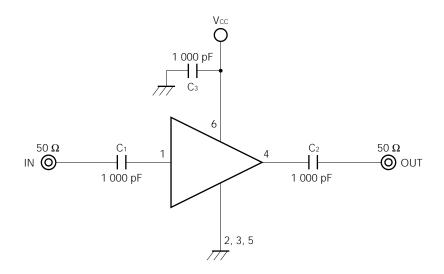
STANDARD CHARACTERISTICS FOR REFERENCE (TA = +25 $^{\circ}$ C, Vcc = 3.0 V, ZL = Zs = 50 Ω)

			μPC2749T	
PARAMETER	SYMBOL	CONDITION	REFERENCE VALUE	UNIT
1 dB compression output	P _{O(1dB)}	f = 1.9 GHz	-12.5	dBm
3rd Order Intermodulation Distortion	IМз	Pout = -25 dBm, f ₁ = 1.9 GHz, f ₂ = 1.902 GHz	-43	dBc
Power Gain	GP	f = 0.9 GHz	14.5	dB
Noise Figure	NF	f = 0.9 GHz	3.2	dB

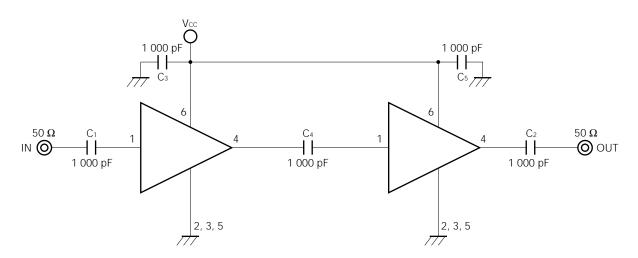
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TEST CIRCUIT



EXAMPLE OF APPLICATION CIRCUIT



The application circuit and their parameters are for references only and are not intended for use in actual design-in's

Capacitors for Vcc, input and output pins

1 000 pF capacitors are recommendable as bypass capacitor for Vcc pin and coupling capacitors for input/output pins.

Bypass capacitor for Vcc pin is intended to minimize Vcc pin's ground impedance. Therefore, stable bias can be supplied against Vcc fluctuation.

Coupling capacitors for input/output pins are intended to minimize RF serial impedance and cut DC.

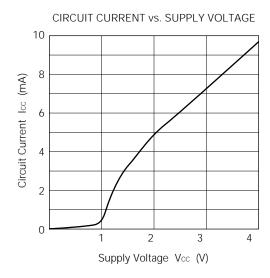
To get flat gain from 100 MHz up, 1 000 pF capacitors are assembled on the test circuit. [Actually, 1000 pF capacitors give flat gain at least 10 MHz. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 2 200 pF. Because the coupling capacitors are determined by the equation

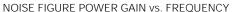
 $C = 1/(2 \pi fZs).$

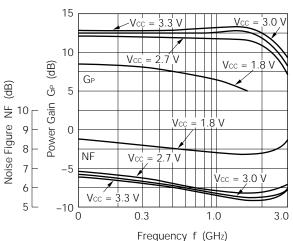
NEC

TYPICAL CHARACTERISTICS — μPC2745T —

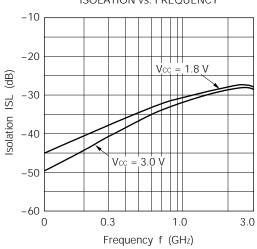
(Unless otherwise specified, TA = +25 °C)



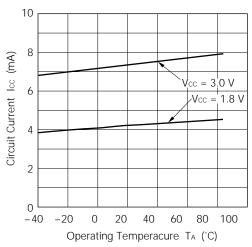




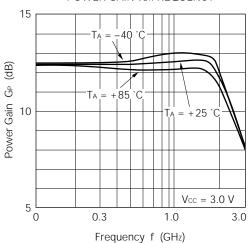
ISOLATION vs. FREQUENCY



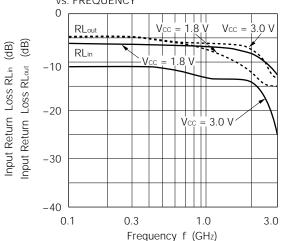
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



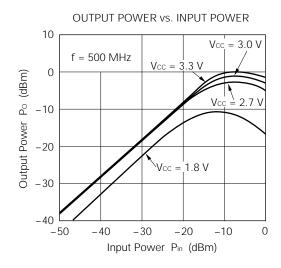
POWER GAIN vs.FREQUENCY

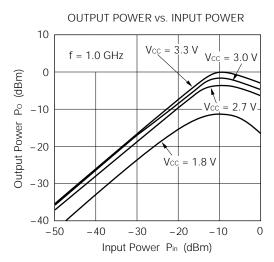


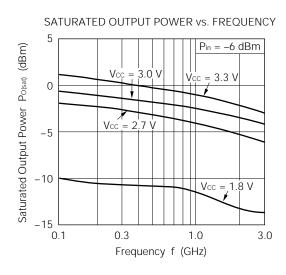
INPUT RETURN LOSS, OUTPUT RETURN LOSS vs. FREQUENCY

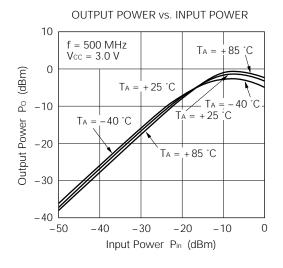


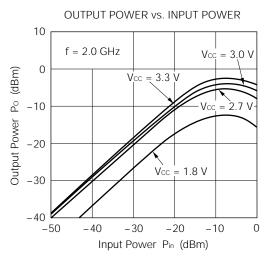
$-\mu$ PC2745T -

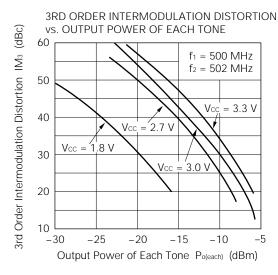










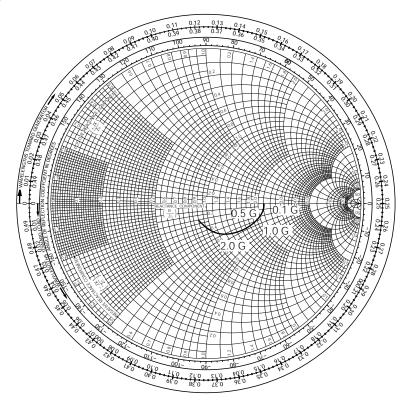




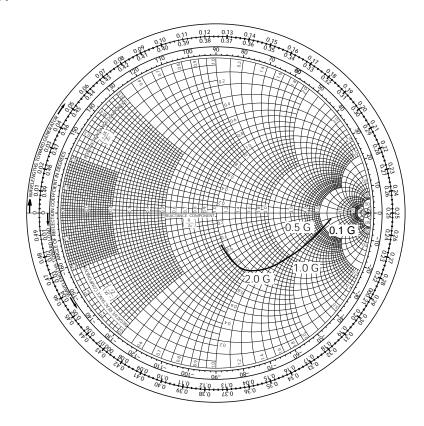
— μ РС2745Т —

S Parameter (Vcc = 3.0 V)

S₁₁-FREQUENCY

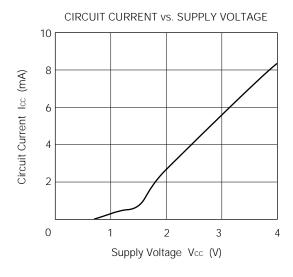


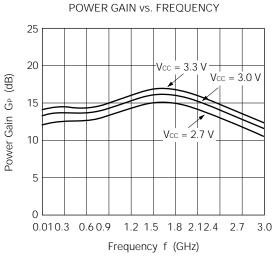
S₂₂-FREQUENCY

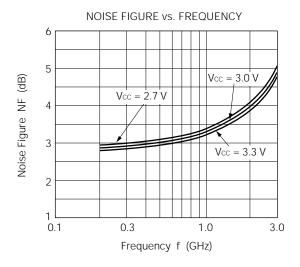


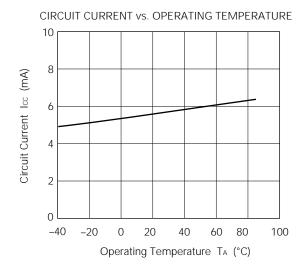
TYPICAL CHARACTERISTICS — µPC2749T —

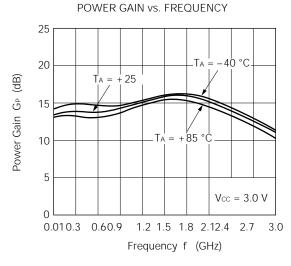
(Unless otherwise specified, TA = +25 °C)





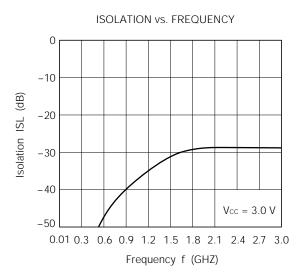


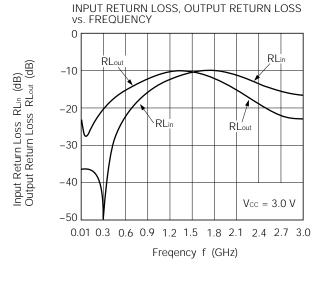


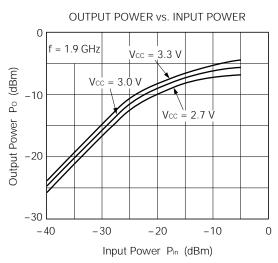


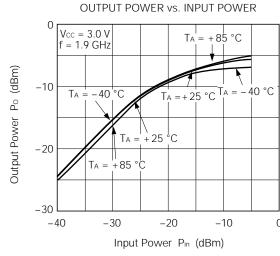


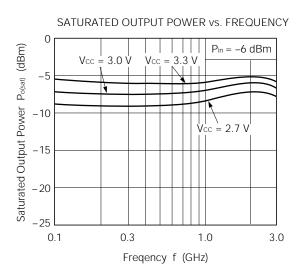
— μPC2749T —

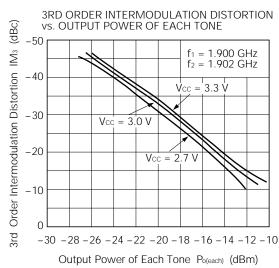








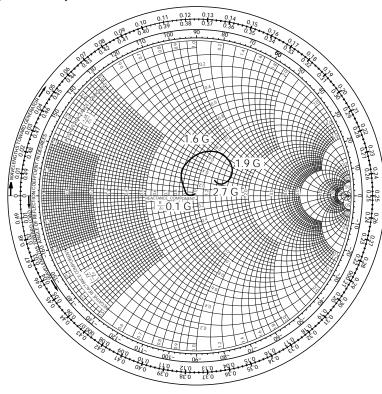




— μ РС2749Т —

S Parameter

S₁₁-FREQUENCY (Vcc = 3.0 V)



 S_{22} -FREQUENCY (Vcc = 3.0 V)

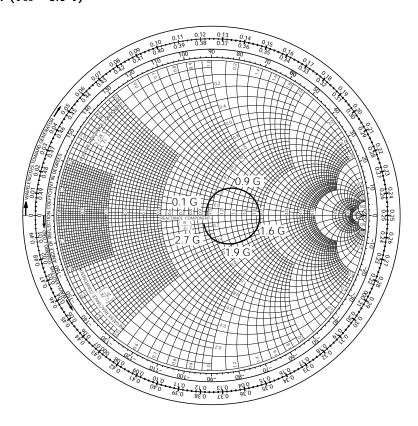
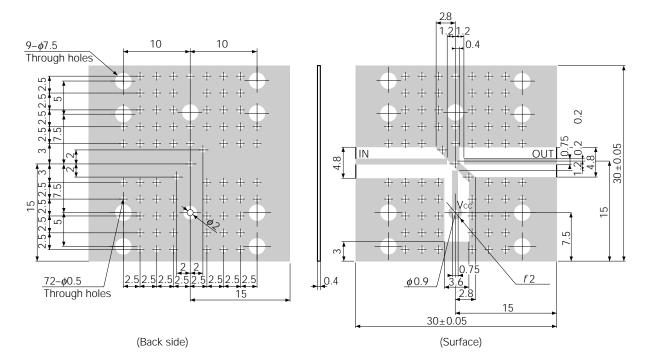




Illustration of evaluation board for the test circuit

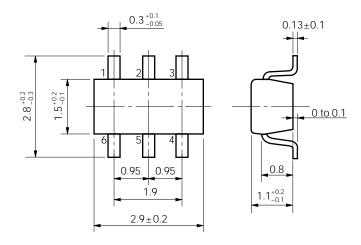


Note

(1) $30 \times 30 \times 0.4$ mm double sided copper clad polyimide board.

(2) Back side: GND pattern
(3) Solder plated on pattern
(4) ⊕⊕⊕ : Through holes

6 PIN MINI MOLD PACKAGE DIMENSIONS (Unit: mm)





NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as wide as possible to keep minimum ground impedance (to prevent undesired oscillation).
- (3) Keep the track length of the ground pins as short as possible.
- (4) Connect a bypass capacitor (e.g. 1 000 pF) to the Vcc Pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered in the following recommended conditions. Other soldering methods and conditions than the recommended conditions are to be consulted with our sales representatives.

μPC2745T, μPC2749T

Soldering method	Soldering conditions	Recommended condition symbol
Infrared ray reflow	Package peak temperature: 235 °C, Hour: within 30 s. (more than 210 °C), Time: 2 times, Limited days: no. Note	IR30-00-2
VPS	Package peak temperature: 215 °C, Hour: within 40 s. (more than 200 °C), Time: 2 times, Limited days: no. Note	VP15-00-2
Wave soldering	Soldering tub temperature: less than 260 °C, Hour: within 10 s. Time: 1 time, Limited days: no.	WS60-00-1
Pin part heating	Pin area temperature: less than 300 °C, Hour: within 10s. Limited days: no. Note	

Note It is the storage days after opening a dry pack, the storage conditions are 25 °C, less than 65 % RH.

Caution The combined use of soldering method is to be avoided (However, except the pin area heating method).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (IEI-1207).

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[MEMO]

[MEMO]



The application circuit and circuit constants shown in this document are for reference only and may not be employed for mass production of the application system.

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Anti-radioactive design is not implemented in this product.

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